

isc N-Channel Mosfet Transistor

FRM240

FEATURES

- 16A, 200V, RDS(on) = 0.24Ω
- Second Generation Rad Hard MOSFET Results
 From New Design Concepts
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

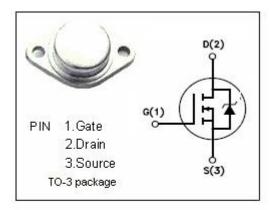
It is specially designed and processed to exhibit minimal characteristic changes to total dose and neutron exposures. Design and processing efforts are also directed to enhance survival to heavy ion (SEE) and/or dose rate (GAMMA DOT) exposure.

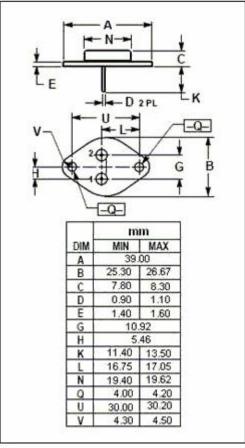


| ABOULUTE MAXIMUM NATINGO(1a-20 C) | | | | | | | |
|-----------------------------------|---|---------|---------------|--|--|--|--|
| SYMBOL | ARAMETER | VALUE | UNIT | | | | |
| V _{DSS} | Drain-Source Voltage (V _{GS} =0) | 200 | V | | | | |
| V _{GS} | Gate-Source Voltage | ±20 | V | | | | |
| I _D | Drain Current-continuous@ TC=25℃ | 16 | Α | | | | |
| | Drain Current-continuous@ TC=100℃ | 10 | Α | | | | |
| I _{DM} | Drain Current-Single Plused | 48 | Α | | | | |
| P _{tot} | Total Dissipation@TC=25℃ | 125 | W | | | | |
| Tj | Max. Operating Junction Temperature | 150 | $^{\circ}$ | | | | |
| T _{stg} | Storage Temperature Range | -55~150 | ${\mathbb C}$ | | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|---|-----|------|
| R _{th j-c} | Thermal Resistance,Junction to Case 1.0 | | °C/W |
| Rth j-a | Rth j-a Thermal Resistance, Junction to Ambient | | °C/W |







isc N-Channel Mosfet Transistor

FRM240

ELECTRICAL CHARACTERISTICS

 T_{C} =25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | MAX | UNIT |
|----------------------|----------------------------------|---|-----|------|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0; I _D =1mA | 200 | | | V |
| V _{GS(TH)} | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =1mA | 2.0 | | 4.0 | V |
| R _{DS(ON)} | Drain-Source On-stage Resistance | V _{GS} =10V; I _D =10A | | | 0.24 | Ω |
| I _{GSS} | Gate Source Leakage Current | V _{GS} =±20V;V _{DS} =0 | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =200V; V _{GS} =0 | | | 25 | μΑ |
| V _{SD} | Diode Forward Voltage | I _S =16A; V _{GS} =0 | | | 1.8 | V |
| t _{d(on)} | Turn-on Delay Time | I_D =16A; V_{DD} =100V; R_{GS} =25 Ω | | | 52 | |
| t _r | Rise Time | | | | 264 | |
| $t_{\sf d(off)}$ | Turn-off Delay Time | | | | 280 | ns |
| t _f | Fall Time | | | | 148 | |



isc N-Channel Mosfet Transistor

FRM240



NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.